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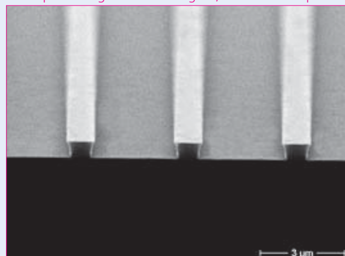
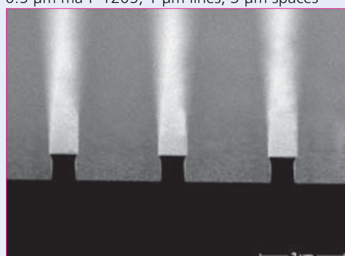
micro resist technology

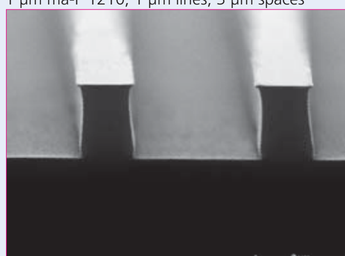
ma-P 1200 — Positive Tone Photoresist Series

Resists for UV Lithography

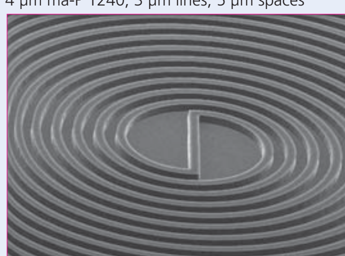
Resist patterning with mask aligner, broadband exposure

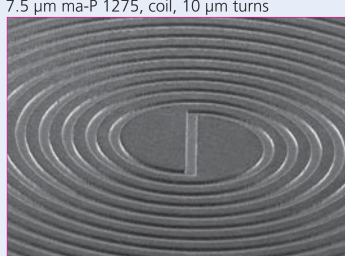

0.5 µm ma-P 1205, 1 µm lines, 3 µm spaces


1 µm ma-P 1210, 1 µm lines, 3 µm spaces


2.5 µm ma-P 1225, 2 µm lines, 4 µm spaces

4 µm ma-P 1240, 3 µm lines, 5 µm spaces


7.5 µm ma-P 1275, coil, 10 µm turns


5 µm electroplated Ni coil, 10 µm turns

Unique features

- Outstanding pattern stability in wet etch processes and acid and alkaline plating baths
- Highly stable in dry etch processes e.g. CHF_3, CF_4, SF_6
- Aqueous alkaline development
- Easy to remove
- Resists available in a variety of viscosities

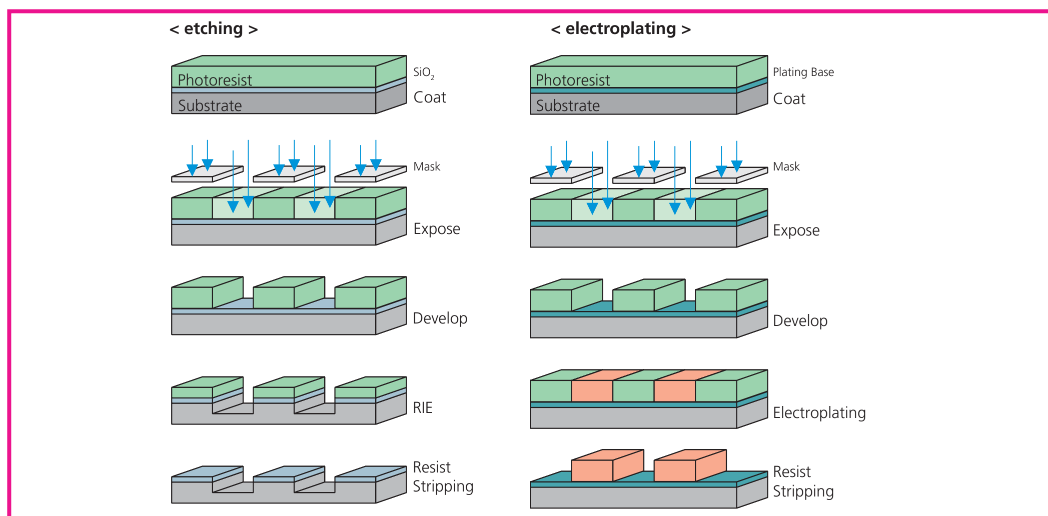
Applications

Mask for etching e.g.
- Si, SiO_2
- Metals
- Semiconductors

Mask for ion implantation

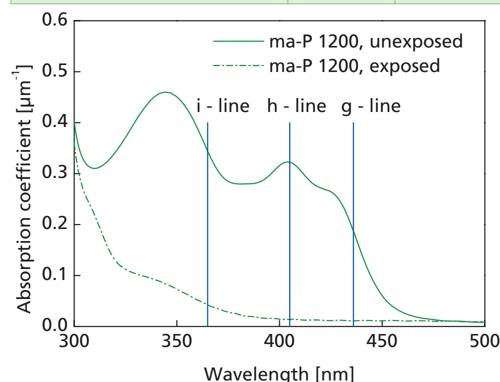
Moulds for electroplating

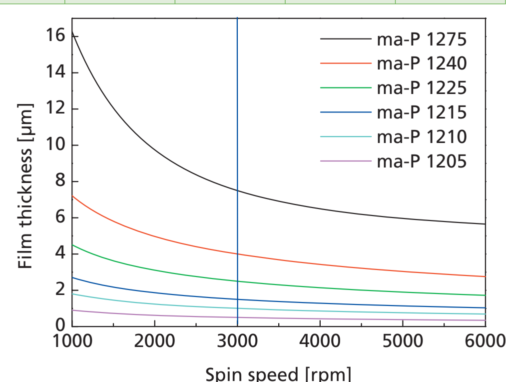
Process flow



Technical data

Resist		ma-P 1205	ma-P 1210	ma-P 1215	ma-P 1225	ma-P 1240	ma-P 1275
Film thickness	µm	0.5	1.0	1.5	2.5	4.0	7.5
Spin coating	U min^{-1} s	3000 30					
Spectral sensitivity		broadband, g-, h-, i-line					
Dose @ 365 nm (broadband exposure)	mJ cm^{-2}	35	35	45	55	110	210





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